



2828

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q64809

Kenji Matsumoto

Appln. No.: 09/873,218

Group Art Unit: 2828

Confirmation No.: 4028

Examiner: Tuan M. NGUYEN

Filed: June 5, 2001

For: SEMICONDUCTOR LASOR FABRICATING METHOD OF THE SAME

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated September 11, 2002, please amend the above-identified application as follows:

IN THE ABSTRACT:

Please amend the abstract as follows:

A semiconductor laser having an S-ARROW structure confining a basic lateral mode light between a pair of guide layers extending with a gap therebetween, which increases a precision of a shape of a guide portion, and is capable of stably emitting a light in the basic lateral mode. In the semiconductor laser having an activation layer and a plurality of layers in parallel with the activation layer, a first groove penetrating through at least some of the layers is formed, and a pair of second grooves extending to predetermined positions toward both sides from the first groove are formed in a specified layer among the layers through which the first groove penetrates. Furthermore, a material having a refractive index higher than that of the

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